



HSD880

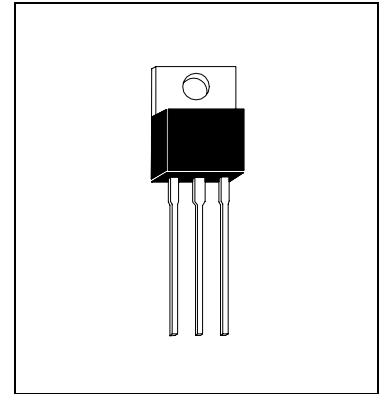
NPN EPITAXIAL PLANAR TRANSISTOR

Description

The HSD880 is designed for low frequency power amplifier applications.

Features

- High DC Current Gain
- High Power Dissipation: PC=30W at TC=25°C



Absolute Maximum Ratings (Ta=25°C)

- Maximum Temperatures
 Storage Temperature -50 ~ +150 °C
 Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
 Total Power Dissipation (Tc=25°C) 30 W
 Total Power Dissipation (Ta=25°C) 1.5 W
- Maximum Voltages and Currents
 BVCBO Collector to Base Voltage 60 V
 BVCEO Collector to Emitter Voltage 60 V
 BVEBO Emitter to Base Voltage 7 V
 IC Collector Current 3 A
 IB Base Current 0.5 A

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	IC=1mA, IE=0
BVCEO	60	-	-	V	IC=50mA, IB=0
ICBO	-	-	100	uA	VCB=60V, IE=0
IEBO	-	-	100	uA	VEB=7V, IC=0
*VCE(sat)	-	-	1	V	IC=3A, IB=0.3A
*VBE(on)	-	-	1	V	IC=0.5A, VCE=5V
*hFE	60	-	300		IC=0.5A, VCE=5V
fT	-	3	-	MHz	IC=500mA, VCE=5V

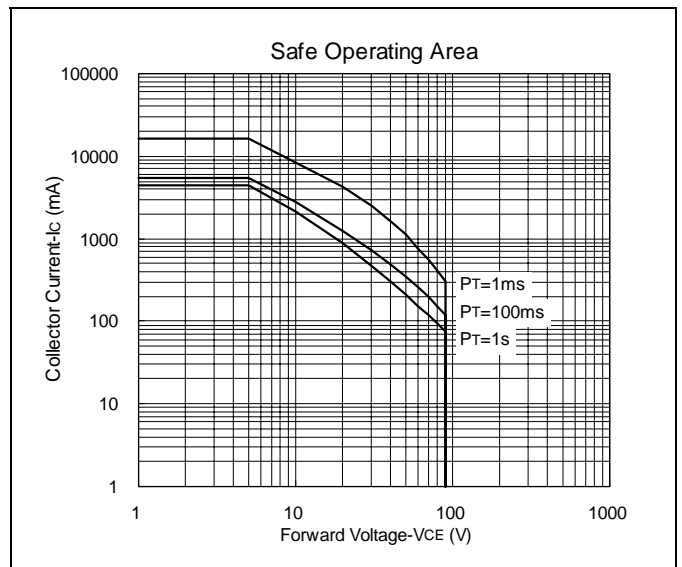
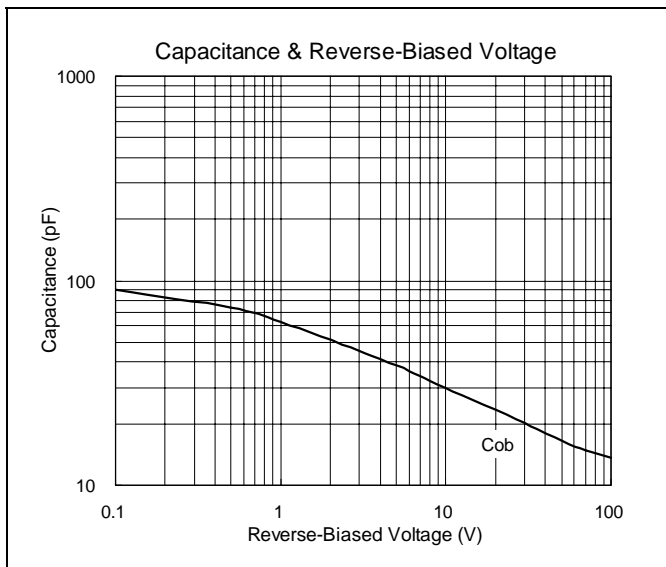
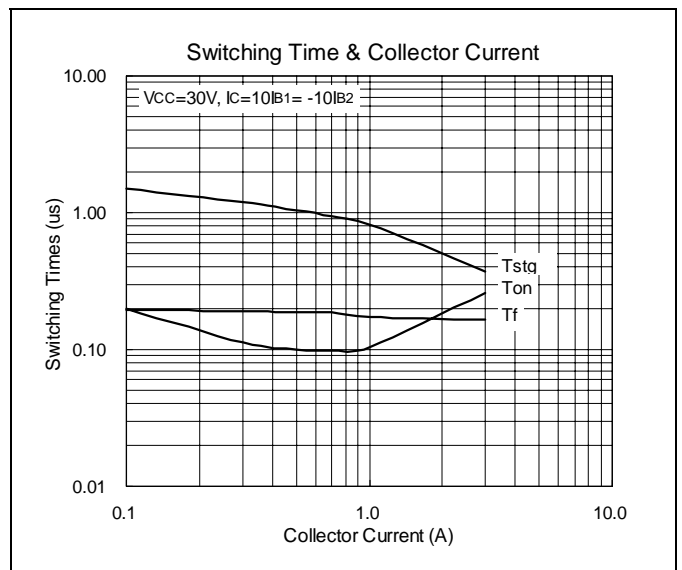
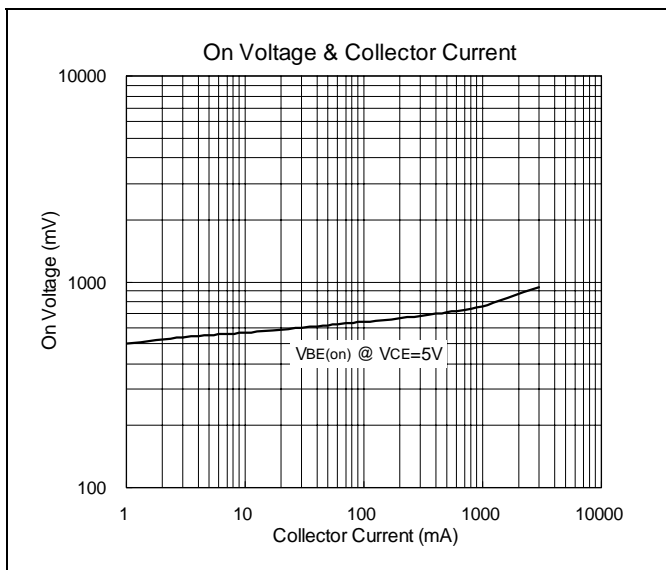
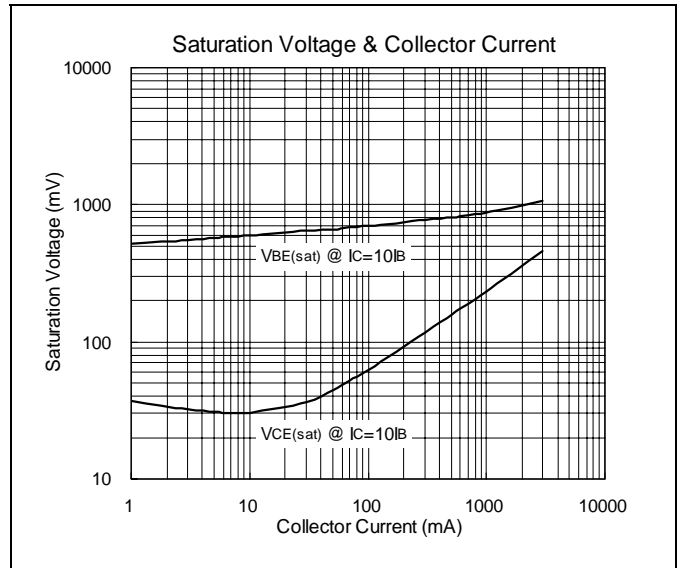
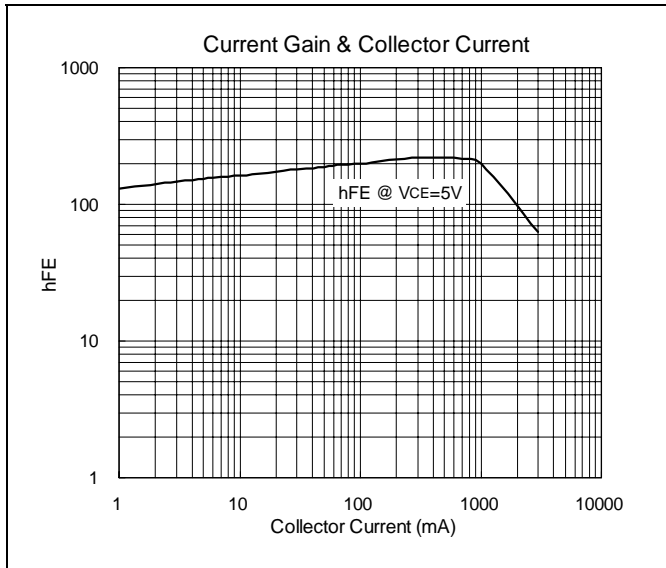
*Pulse Test : Pulse Width ≤380us, Duty Cycle≤2%

Classification Of hFE

Rank	O	Y	GR
Range	60-120	100-200	150-300

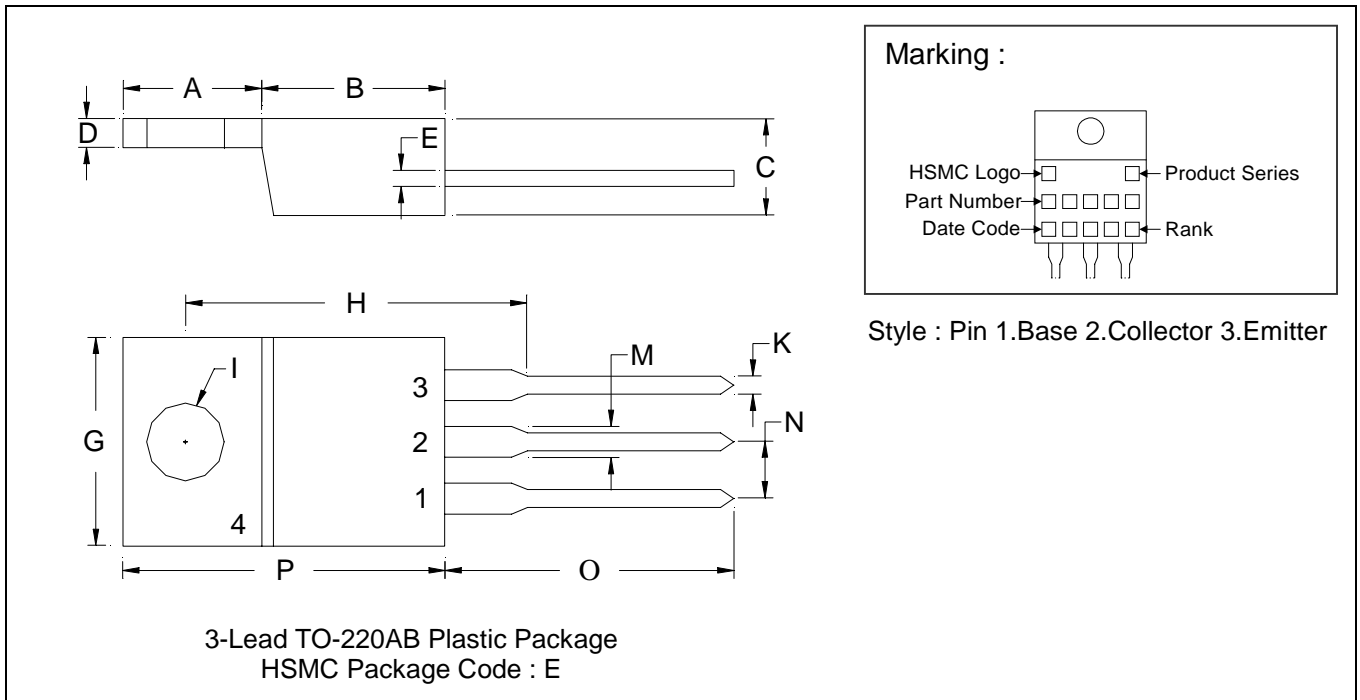


Characteristics Curve





TO-220AB Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.2197	0.2949	5.58	7.49	I	-	*0.1508	-	*3.83
B	0.3299	0.3504	8.38	8.90	K	0.0295	0.0374	0.75	0.95
C	0.1732	0.185	4.40	4.70	M	0.0449	0.0551	1.14	1.40
D	0.0453	0.0547	1.15	1.39	N	-	*0.1000	-	*2.54
E	0.0138	0.0236	0.35	0.60	O	0.5000	0.5618	12.70	14.27
G	0.3803	0.4047	9.66	10.28	P	0.5701	0.6248	14.48	15.87
H	-	*0.6398	-	*16.25					

Notes : 1.Dimension and tolerance based on our Spec. dated Sep. 07,1997.
 2.Controlling dimension : millimeters.
 3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

Material :

- Lead : 42 Alloy ; solder plating
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0

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